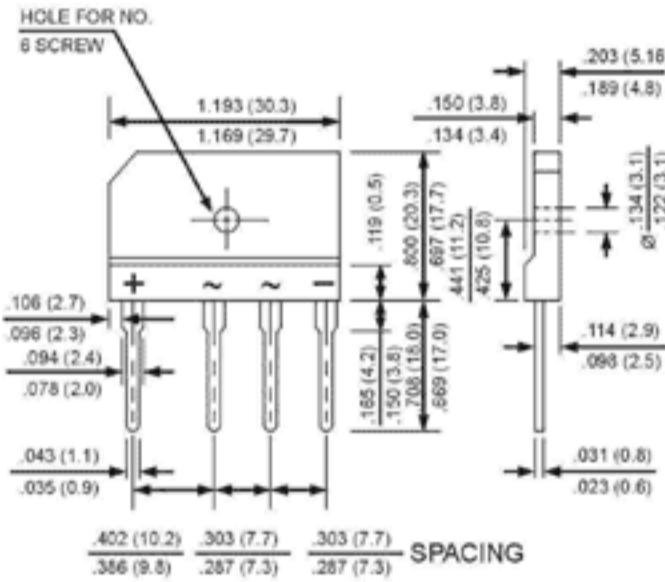


## SILICON BRIDGE RECTIFIERS

REVERSE VOLTAGE - 50 to 1000 Volts  
 FORWARD CURRENT - 8.0 Amperes

## FEATURES

- Rating to 1000V PRV
- Ideal for printed circuit board
- Low forward voltage drop, high current capability
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- The plastic material has UL flammability classification 94V-0



Dimensions in inches and (millimeters)

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	KBJ 8A	KBJ 8B	KBJ 8D	KBJ 8G	KBJ 8J	KBJ 8K	KBJ 8M	UNIT
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Maximum DC Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Maximum Average Forward (with heatsink Note 2) Rectified Current @ T <sub>c</sub> =100°C (without heatsink)	I(AV)				8.0	2.9			A
Peak Forward Surge Current 8.3ms single half sine-wave super imposed on rated load (JEDEC Method)	I <sub>FSM</sub>				200				A
Maximum Forward Voltage at 4.0A DC	V <sub>F</sub>				1.0				V
Maximum DC Reverse Current @ T <sub>j</sub> = 25 °C at Rated DC Blocking Voltage @ T <sub>j</sub> =125°C	I <sub>R</sub>				5.0	500			uA
I <sup>2</sup> t Rating for fusing (t<8.3ms)	I <sup>2</sup> t				120				A·S
Typical Junction Capacitance per element (Note 1)	C <sub>J</sub>				55				pF
Typical Thermal Resistance (Note 2)	R <sub>th</sub> C				1.6				°C/W
Operating Temperature Range	T <sub>j</sub>				-40 to +125				°C
Storage Temperature Range	T <sub>STG</sub>				-40 to +125				°C

NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Device mounted on 100mm x 100mm x 1.6mm Cu Plate Heatsink.